

1N4001G THRU 1N4007G

TECHNICAL SPECIFICATIONS OF SILICON RECTIFIER

VOLTAGE: 50-1000V

CURRENT: 1.0A

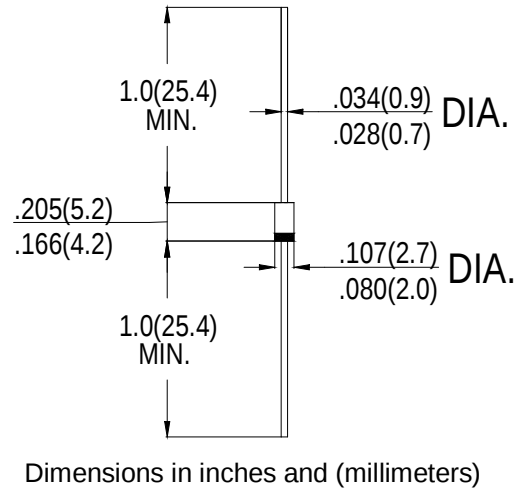
FEATURES

- High reliability
- Low leakage
- Low forward voltage drop
- High current capability

MECHANICAL DATA

- **Case:** Molded plastic
- **Epoxy:** UL94V-0 rate flame retardant
- **Lead:** MIL-STD- 202E, Method 208 guaranteed
- **Polarity:** Color band denotes cathode end
- **Mounting position:** Any
- **Weight:** 0.33 grams

DO-41



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

		SYMBOL	1N4001G	1N4002G	1N4003G	1N4004G	1N4005G	1N4006G	1N4007G	units
Maximum Recurrent Peak Reverse Voltage		V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage		V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage		V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward rectified Current at T _A =75°C		I_o	1.0							A
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rate load (JEDEC method)		I_{FSM}	30							A
Maximum Instantaneous forward Voltage at 1.0A DC		V_F	1.1							V
Maximum DC Reverse Current at Rated DC Blocking Voltage	@ T _A =25°C	I_R	5.0							μA
	@ T _A =100°C		500							
Maximum Full Load Reverse Current Average Full Cycle .375”(9.5mm) lead length at T _L =75°C			30							
Typical Junction Capacitance (Note)		C_J	15							pF
Typical Thermal Resistance		R_{θJA}	50							°C/W

Notes: Measured at 1MHz and applied reverse voltage of 4.0 volts